



## 2024- 2025 MPW schedule

Last updated: October 16, 2024

MPW name	Fab	Processes	Tape-In	Ship Date
PH18DA - B5603	NPB - Fab 3	SiPho 0.18um	2-20-24	10-25-24
SB*18 - B5611	NPB - Fab 3	SiGe BiCMOS 0.18um	6-11-24	12-19-24
CA18 - B5613	NPB - Fab 3	RFCMOS 0.18um	7-16-24	12-27-24
SB*18 - B5615	NPB - Fab 3	SiGe BiCMOS 0.18um	8-13-24	2-20-25
PH18DA - B5614	NPB - Fab 3	SiPho 0.18um	8-20-24	4-25-25
PH18M* - B5617	NPB - Fab 3	SiPho 0.18um	9-10-24	1-24-25
SB*18 - B5619	NPB - Fab 3	SiGe BiCMOS 0.18um	10-08-24	4-17-25
CS18* - B5616	MH - Fab 2	CMOS-SOI 0.18um	10-29-24	
Q4 2024	NM – Fab 11	TPS65MSPM	10-15-24	
33rd MPW - Uozu, Japan	TPSCo - Fab 7	300mm Silicon Photonics: TPS45PHD	10-28-24	
CA18 - B5621	NPB - Fab 3	RFCMOS 0.18um	11-05-24	4-18-25
SH524T18NOV	MH - Fab 2	CIS 0.18u Image Sensor CMOS+ 0.16u, 0.18u RF, RFID, PM	11-14-24 11-21-24	
SB*18 - B5622	NPB - Fab 3	SiGe BiCMOS 0.18um	11-19-24	5-29-25
31st MPW - Tonami, Japan	TPSCo - Fab 5	CMOS 0.18u & 0.16u, PM, PM_SOI	11-25-24	
SB*18 – B6000	NPB - Fab 3	SiGe BiCMOS 0.18um	1-14-25	7-24-25
SBC18HE5PCA - B6001	NPB - Fab 3	SiGe BiCMOS 0.18um with PCM RF Switch	1-28-25	
Q1 2025	NM - Fab 11	TPS65MSPM	2-04-25	
CA18 - B6002	NPB - Fab 3	RFCMOS 0.18um	2-11-25	7-25-25
SH125T18FEB	MH - Fab 2	0.18 BSI, Stacking on 0.13	2-12-25	
32nd MPW - Tonami, Japan	TPSCo - Fab 5	CMOS 0.18u & 0.16u, PM, PM_SOI	2-25-25	
PH18M* - B6003	NPB - Fab 3	SiPho 0.18um	2-25-25	7-11-25
CS18QT2PCA - B6004	NPB - Fab 3	CMOS-SOI 0.18um with PCM RF Switch	3-04-25	
34th MPW - Uozu, Japan	TPSCo - Fab 7	RFSOI, 65nm : TPS90RSB2, TPS65RSA2/RSB2/RSC	3-10-25	
35th MPW - Uozu, Japan	TPSCo - Fab 7	CMOS, PM, RFCMOS & SiGe, 65nm : TPS65SLA/SLC, TPS65PMA/PMB/MSA/MSB, TPS65RF, TPS65SG	3-24-25	
PH18DA - B6006	NPB - Fab 3	SiPho 0.18um	3-25-25	12-02-25
SB*18 - B6007	TJT - Fab 9	SiGe BiCMOS 0.18um	4-08-25	
SH225T18APRIL	MH - Fab 2	CIS 0.18u Image Sensor CMOS+ 0.16u, 0.18u RF, RFID, PM	4-10-25 4-17-25	
36th MPW - Uozu, Japan	TPSCo - Fab 7	300mm Silicon Photonics: TPS45PHD	4-14-25	

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SBC18HE5PCA - B6008	NPB - Fab 3	SiGe BiCMOS 0.18um with PCM RF Switch	4-22-25	
CA18 - B6009	NPB - Fab 3	RFCMOS 0.18um	5-06-25	10-17-25
PH18M* - B6010	NPB - Fab 3	SiPho 0.18um	5-20-25	10-03-25
33rd MPW - Tonami, Japan	TPSCo - Fab 5	CMOS 0.18u & 0.16u, PM, PM_SOI	5-26-25	
SB*18 - B6011	NPB - Fab 3	SiGe BiCMOS 0.18um	6-03-25	12-11-25
CS18* - B6012	MH - Fab 2	CMOS-SOI 0.18um	6-17-25	
SB*/CA13* - B6013	NPB - Fab 3	SiGe BiCMOS/RF CMOS 0.13um	7-01-25	2-27-26
SBC18HE5PCA - B6014	NPB - Fab 3	SiGe BiCMOS 0.18um with PCM RF Switch	7-15-25	
SB*18 - B6015	NPB - Fab 3	SiGe BiCMOS 0.18um	7-29-25	2-05-26
PH18DA - B6016	NPB - Fab 3	SiPho 0.18um	8-12-25	4-17-26
34th MPW - Tonami, Japan	TPSCo - Fab 5	CMOS 0.18u & 0.16u, PM, PM_SOI	8-25-25	
CA18 - B6017	NPB - Fab 3	RFCMOS 0.18um	8-26-25	2-06-26
CS18QT2PCA - B6018	NPB - Fab 3	CMOS-SOI 0.18um with PCM RF Switch	9-09-25	
PH18M* - B6019	NPB - Fab 3	SiPho 0.18um	9-23-25	2-06-26
37th MPW - Uozu, Japan	TPSCo - Fab 7	CMOS, PM, RFCMOS & SiGe, 65nm : TPS65SLA/SLC, TPS65PMA/PMB/MSA/MSB, TPS65RF, TPS65SG	9-29-25	
SB*18 - B6020	NPB - Fab 3	SiGe BiCMOS 0.18um	10-07-25	4-16-26
SBC18HE5PCA - B6021	NPB - Fab 3	SiGe BiCMOS 0.18um with PCM RF Switch	10-21-25	
38th MPW - Uozu, Japan	TPSCo - Fab 7	300mm Silicon Photonics: TPS45PHD	10-27-25	
PH18M* - B6022	NPB - Fab 3	SiPho 0.18um	11-04-25	3-20-26
SH325T18NOV	MH - Fab 2	CIS 0.18u Image Sensor CMOS+ 0.16u, 0.18u RF, RFID, PM	11-17-25 11-23-25	
CS18* - B6023	MH - Fab 2	CMOS-SOI 0.18um	11-18-25	
35th MPW - Tonami, Japan	TPSCo - Fab 5	CMOS 0.18u & 0.16u, PM, PM_SOI	11-25-25	

Notes: "Shuttles" (SH\*) are run at Fab 2

\* 0.13u MH – fab 2 Shuttle / MPW slots will be considered per needs

Please contact your customer account manager for additional information.

Fab2 - Tower Semiconductor 200mm wafer fabrication facility at Migdal Ha'emek, Israel

Fab3 - Tower Semiconductor 200mm wafer fabrication facility at Newport Beach, CA

Fab5 - Tower Semiconductor 200mm wafer fabrication facility at Tonami, Japan

Fab7 - Tower Semiconductor 300mm wafer fabrication facility at Uozu, Japan

Fab9 - Tower Semiconductor 200mm wafer fabrication facility at San Antonio, TX

Fab11 - Tower Semiconductor 300mm wafer fabrication facility at Rio Rancho, NM